

این دیتاشیت توسط توکل الکترونیک تهیه و ارائه شده است.  
جهت مشاهده قیمت، موجودی و ثبت سفارش این قطعه به وبسایت توکل الکترونیک مراجعه فرمایید.



مشاهده قیمت و خرید

برای خرید و مشاهده سایر محصولات کلیک کنید



isc®

INCHARGE SEMICONDUCTOR

## isc N-Channel MOSFET Transistor

2SK2645

## • FEATURES

- Drain Current  $I_D = 9A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DS} = 600V(\text{Min})$
- High speed Switching
- Repetitive Avalanche rated
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## • APPLICATIONS

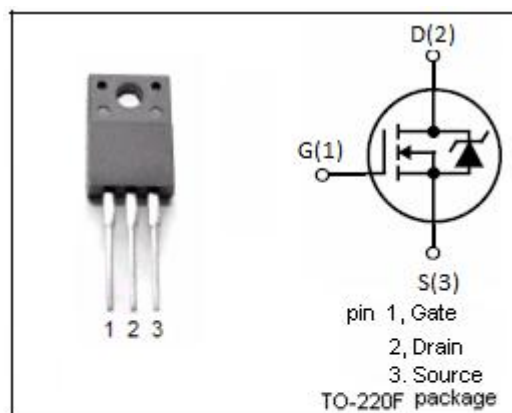
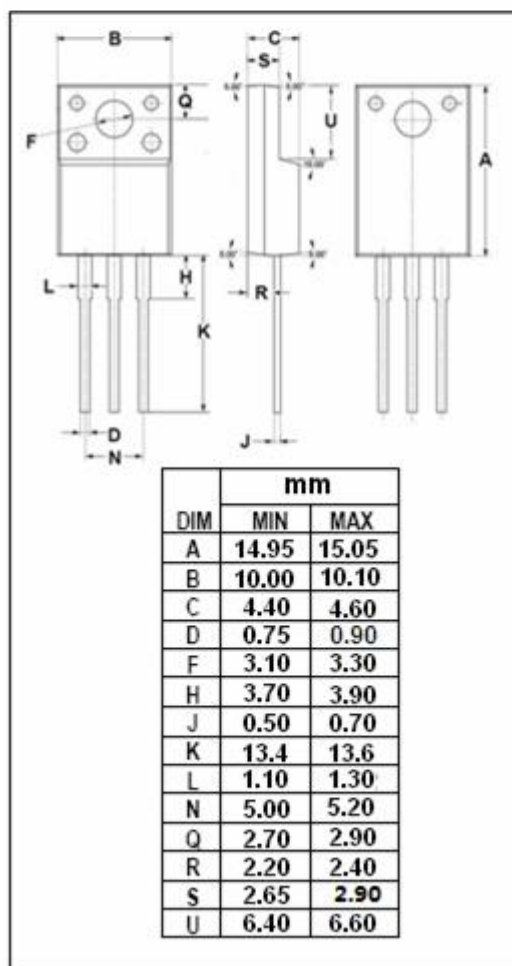
- DC-DC converter, Switching Regulators, General Purpose Power Amplifier

• ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )

| SYMBOL    | PARAMETER                              | VALUE    | UNIT       |
|-----------|----------------------------------------|----------|------------|
| $V_{DS}$  | Drain-Source Voltage                   | 600      | V          |
| $V_{GS}$  | Gate-Source Voltage-Continuous         | $\pm 30$ | V          |
| $I_D$     | Drain Current-Continuous               | 9        | A          |
| $P_D$     | Total Dissipation @ $T_C = 25^\circ C$ | 50       | W          |
| $T_j$     | Max. Operating Junction Temperature    | 150      | $^\circ C$ |
| $T_{stg}$ | Storage Temperature                    | -55~150  | $^\circ C$ |

## • THERMAL CHARACTERISTICS

| SYMBOL       | PARAMETER                               | MAX  | UNIT         |
|--------------|-----------------------------------------|------|--------------|
| $R_{th j-c}$ | Thermal Resistance, Junction to Case    | 2.5  | $^\circ C/W$ |
| $R_{th j-a}$ | Thermal Resistance, Junction to Ambient | 62.5 | $^\circ C/W$ |



**isc N-Channel MOSFET Transistor****2SK2645****• ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

| SYMBOL               | PARAMETER                       | CONDITIONS                                              | MIN | TYPE | MAX | UNIT |
|----------------------|---------------------------------|---------------------------------------------------------|-----|------|-----|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> =1mA                | 600 |      |     | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA | 3.5 |      | 4.5 | V    |
| V <sub>SD</sub>      | Forward voltage(Diode)          | I <sub>DR</sub> = 9A; V <sub>GS</sub> = 0               |     |      | 1.5 | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 4A              |     | 1.0  | 1.2 | Ω    |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0             |     |      | 100 | nA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> =600V; V <sub>GS</sub> = 0              |     |      | 500 | μA   |

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